

MITSUBISHI IGBT MODULES

CM75TL-24NF

HIGH POWER SWITCHING USE

CM75TL-24NF



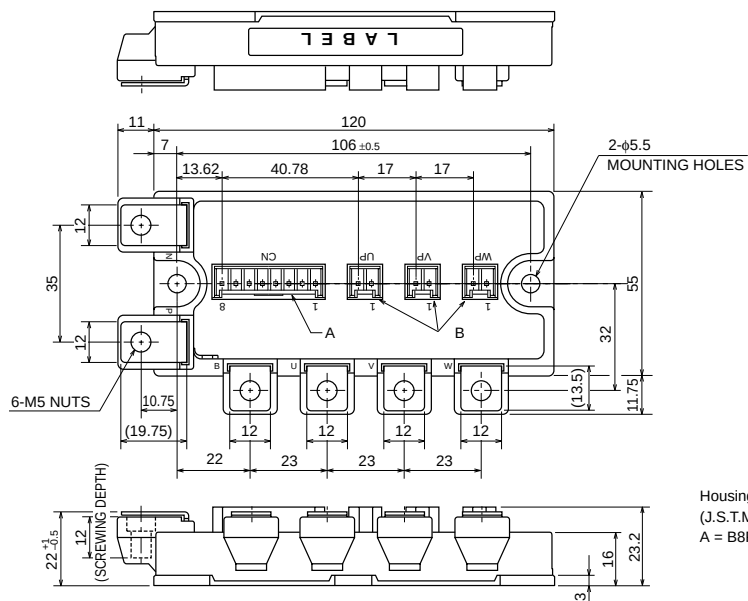
- IC 75A
- VCES 1200V
- Insulated Type
- 6-elements in a pack

APPLICATION

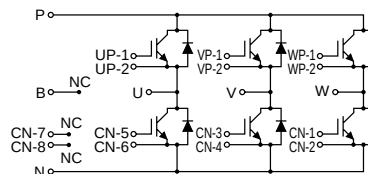
AC drive inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Housing Type of A and B
(J.S.T.Mfg.Co.Ltd)
A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

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ABSOLUTE MAXIMUM RATINGS (Tj = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
VCES	Collector-emitter voltage	G-E Short	1200	V
VGES	Gate-emitter voltage	C-E Short	±20	V
IC	Collector current	DC, Tc = 87°C*1	75	A
ICM		Pulse (Note 2)	150	A
IE (Note 1)			75	A
IEM (Note 1)	Emitter current	Pulse (Note 2)	150	A
PC (Note 3)		Tc = 25°C	520	W
Tj	Junction temperature		−40 ~ +150	°C
Tstg	Storage temperature		−40 ~ +125	°C
Viso	Isolation voltage	Main Terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M5	2.5 ~ 3.5	N • m
—		Mounting holes M5	2.5 ~ 3.5	N • m
—	Weight	Typical value	350	g

ELECTRICAL CHARACTERISTICS (Tj = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 7.5mA, VCE = 10V	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 75A, VGE = 15V	—	2.1	3.0	V
		Tj = 125°C	—	2.4	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	11.5	nF
Coēs	Output capacitance		—	—	1.0	nF
Cres	Reverse transfer capacitance		—	—	0.23	nF
QG	Total gate charge	VCC = 600V, IC = 75A, VGE = 15V	—	338	—	nC
td(on)	Turn-on delay time	VCC = 600V, IC = 75A VGE1 = VGE2 = 15V RG = 4.2Ω, Inductive load switching operation IE = 75A	—	—	100	ns
tr	Turn-on rise time		—	—	50	ns
td(off)	Turn-off delay time		—	—	300	ns
tr	Turn-off fall time		—	—	350	ns
t _{rr} (Note 1)	Reverse recovery time		—	—	120	ns
Q _{rr} (Note 1)	Reverse recovery charge		—	3	—	μC
VEC(Note 1)	Emitter-collector voltage	IE = 75A, VGE = 0V	—	—	3.8	V
Rth(j-c)Q	Thermal resistance	IGBT part (1/6 module)*1	—	—	0.24	°C/W
Rth(j-c)R		FWDi part (1/6 module)*1	—	—	0.36	°C/W
Rth(c-f)	Contact thermal resistance	Case to fin, Thermal compound Applied (1/6 module)*2	—	0.085	—	°C/W
RG	External gate resistance		4.2	—	63	Ω

*1 : Tc measured point is just under the chips.

If you use this value, Rth(f-a) should be measured just under the chips.

*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

Note 1. IE, VEC, trr & Qrr represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (Tj) does not exceed Tjmax rating.

3. Junction temperature (Tj) should not increase beyond 150°C.

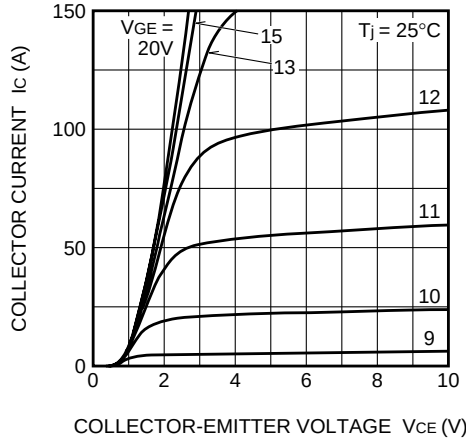
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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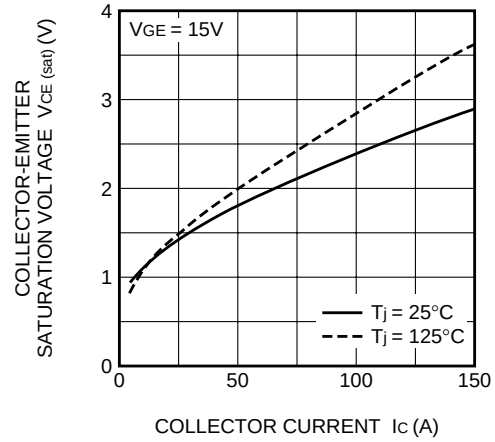
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

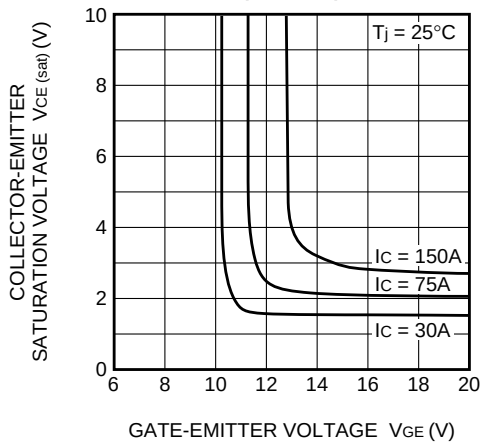
OUTPUT CHARACTERISTICS
(TYPICAL)



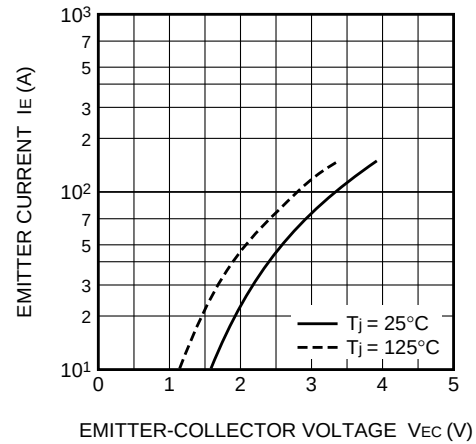
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



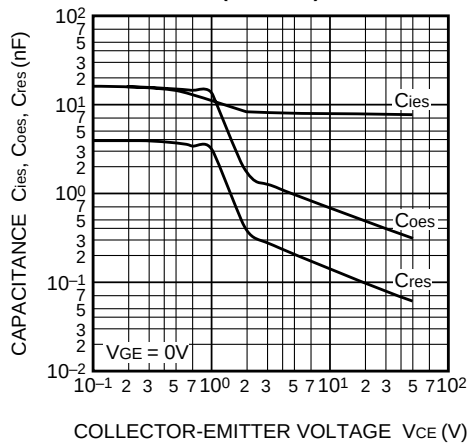
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



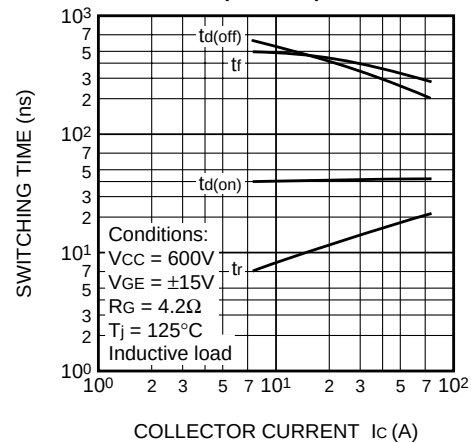
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



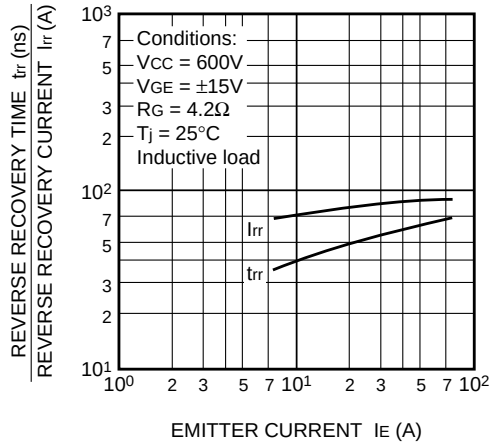
CAPACITANCE- V_{ce}
CHARACTERISTICS
(TYPICAL)



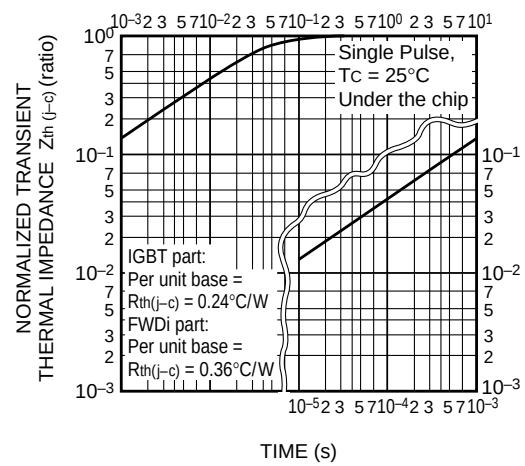
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



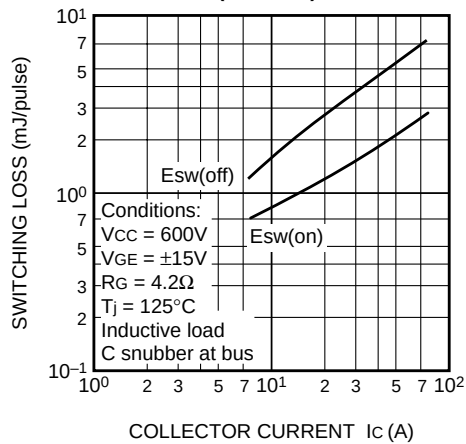
REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)



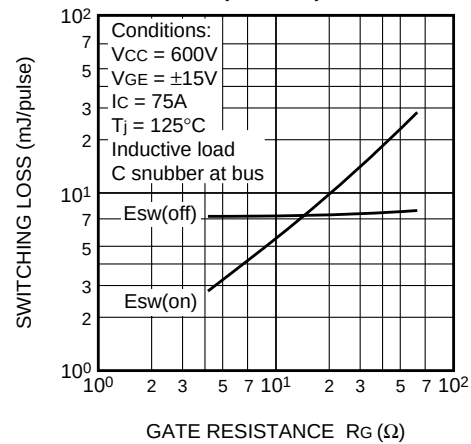
TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part & FWDi part)



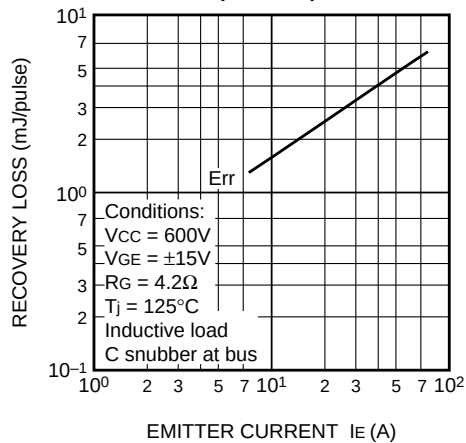
SWITCHING LOSS vs.
COLLECTOR CURRENT
(TYPICAL)



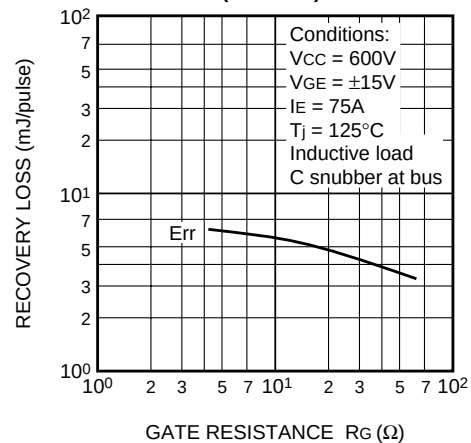
SWITCHING LOSS vs.
GATE RESISTANCE
(TYPICAL)



RECOVERY LOSS vs. I_E
(TYPICAL)



RECOVERY LOSS vs.
GATE RESISTANCE
(TYPICAL)



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